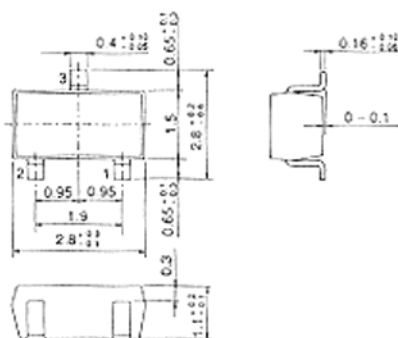


2SC2620

SILICON NPN EPITAXIAL PLANAR
VHF AMPLIFIER, LOCAL OSCILLATOR

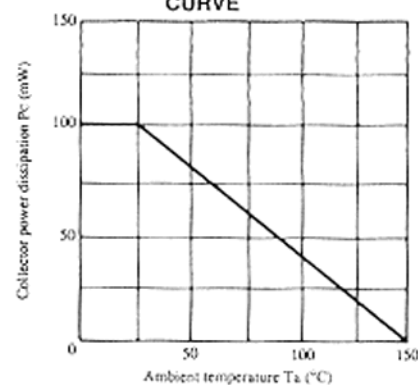


(MPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2620	Unit
Collector to base voltage	V _{CB0}	30	V
Collector to emitter voltage	V _{CE0}	20	V
Emitter to base voltage	V _{EB0}	4	V
Collector current	I _C	20	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	30	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	20	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	4	—	—	V
Collector cutoff current	I _{CB0}	V _{CB} = 10V, I _E = 0	—	—	0.5	μA
Emitter cutoff current	I _{EB0}	V _{EB} = 2V, I _C = 0	—	—	0.5	μA
DC current transfer ratio	h _{FE} *	V _{CE} = 6V, I _C = 1mA	60	—	200	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 20mA, I _B = 4mA	—	0.17	—	V
Base to emitter voltage	V _{BE}	V _{CE} = 6V, I _C = 1mA	—	0.72	—	V
Gain bandwidth product	f _T	V _{CE} = 6V, I _C = 5mA	—	940	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	0.9	—	pF

* The 2SC2620 is grouped by h_{FE} as follows.

Grade	B	C
Max	QB	QC
h _{FE}	60 to 120	100 to 200

■ See characteristic curves of 2SC535.